

**BCW89**  
**SURFACE MOUNT**  
**PNP SILICON TRANSISTOR**



**SOT-23 CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR BCW89 is a Silicon PNP Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose applications.

**MARKING CODE: H3**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Emitter Voltage	$V_{CEO}$	60	V
Collector-Base Voltage	$V_{CES}$	60	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Continuous Collector Current	$I_C$	500	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^\circ\text{C}/\text{W}$

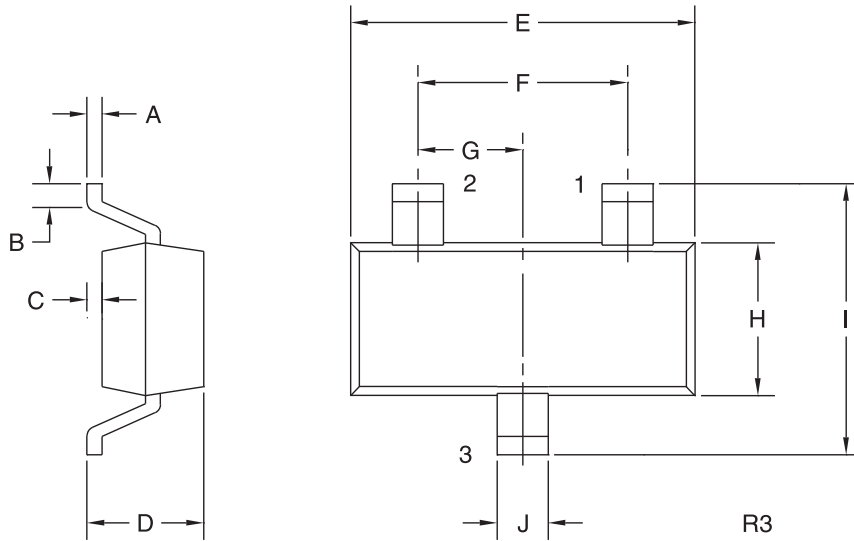
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=20\text{V}$		100	nA
$I_{CBO}$	$V_{CB}=20\text{V}, T_A=100^\circ\text{C}$		10	$\mu\text{A}$
$BV_{CBO}$	$I_C=10\mu\text{A}$	80		V
$BV_{CEO}$	$I_C=2.0\text{mA}$	60		V
$BV_{CES}$	$I_C=10\mu\text{A}$	60		V
$BV_{EBO}$	$I_C=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		300	mV
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	600	750	mV
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	120	260	
NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=2.0\text{k}\Omega$ $f=1.0\text{kHz}, B=200\text{Hz}$		10	dB

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**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**  
1) BASE  
2) EMITTER  
3) COLLECTOR

**MARKING CODE: H3**

<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (20-November 2009)